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Gate Electrode Deposition and Structure Formed Thereby

Abstract

A method includes depositing a first work function tuning layer over a gate dielectric layer using an atomic layer deposition process. The atomic layer deposition process comprises depositing one or more first nitride monolayers; and depositing one or more carbide monolayers over the one or more first nitride monolayers. The method further includes depositing an adhesion layer of the first work function tuning layer; and depositing a conductive material over the adhesion layer.

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Background/Summary

PRIORITY CLAIM AND CROSS-REFERENCE [0001] This application is a continuation of U.S. application Ser. No. 18/079,171, filed on Dec. 12, 2022, which is a continuation of U.S. application Ser. No. 17,078,655, filed Oct. 23, 2020, now U.S. Pat. No. 11,527,621 issued on Dec. 13, 2022, which claims the benefit of U.S. Provisional Application No. 63/061,349, filed on Aug. 5, 2020, which applications are hereby incorporated herein by reference.

BACKGROUND

[0002] Semiconductor devices are used in a variety of electronic applications, such as, for example, personal computers, cell phones, digital cameras, and other electronic equipment. Semiconductor devices are typically fabricated by sequentially depositing insulating or dielectric layers, conductive layers, and semiconductor layers of material over a semiconductor substrate, and patterning the various material layers using lithography to form circuit components and elements thereon.

[0003] The semiconductor industry continues to improve the integration density of various electronic components (e.g., transistors, diodes, resistors, capacitors, etc.) by continual reductions in minimum feature size, which allow more components to be integrated into a given area.

Description

BRIEF DESCRIPTION OF THE DRAWINGS

[0004] Aspects of the present disclosure are best understood from the following detailed description when read with the accompanying figures. It is noted that, in accordance with the standard practice in the industry, various features are not drawn to scale. In fact, the dimensions of the various features may be arbitrarily increased or reduced for clarity of discussion.

[0005] FIG. 1 illustrates an example of a FinFET in a three-dimensional view, in accordance with some embodiments.

[0006] FIGS. 2, 3, 4, 5, 6, 7, 8A, 8B, 9A, 9B, 10A, 10B, 10C, 10D, 11A, 11B, 12A, 12B, 13A, 13B, 14A, 14B, 14C, 15A, 15B, 15C, 15D, 17A, 17B, 18A, and 18B are cross-sectional views of intermediate stages in the manufacturing of FinFETs, in accordance with some embodiments.

[0007] FIGS. 16A and 16B illustrate deposition processes, in accordance with some embodiments.

DETAILED DESCRIPTION

[0008] The following disclosure provides many different embodiments, or examples, for implementing different features of the invention. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. For example, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed between the first and second features, such that the first and second features may not be in direct contact. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments

and/or configurations discussed.

[0009] Further, spatially relative terms, such as “beneath,” “below,” “lower,” “above,” “upper” and the like, may be used herein for ease of description to describe one element or feature's relationship to another element(s) or feature(s) as illustrated in the figures. The spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. The apparatus may be otherwise oriented (rotated **90** degrees or at other orientations) and the spatially relative descriptors used herein may likewise be interpreted accordingly.

[0010] Various embodiments provide a method of depositing a work function metal (WFM) layer of a gate electrode for improved work function tuning. In some embodiments, the WFM layer is a p-type layer that is formed by an atomic layer deposition (ALD) process. The ALD process may deposit a combination of nitride monolayers (e.g., titanium nitride, tantalum nitride, or the like) and carbide monolayers (e.g., titanium carbide, tantalum carbide, or the like). By adjusting the ratio of a quantity of carbide monolayers to a quantity of nitride monolayers that are deposited, a work function of the gate electrode can be more precisely tuned. For example, a higher ratio carbon to nitrogen in the WFM layer may result in a lower work function (e.g., more n-type), and a lower ratio of carbon to nitrogen in the WFM layer may result in a higher work function (e.g., more p-type).

[0011] FIG. **1** illustrates an example of a FinFET in a three-dimensional view, in accordance with some embodiments. The FinFET comprises a fin **52** on a substrate **50** (e.g., a semiconductor substrate). Isolation regions **56** are disposed in the substrate **50**, and the fin **52** protrudes above and from between neighboring isolation regions **56**. Although the isolation regions **56** are described/illustrated as being separate from the substrate **50**, as used herein the term “substrate” may be used to refer to just the semiconductor substrate or a semiconductor substrate inclusive of isolation regions. Additionally, although the fin **52** is illustrated as a single, continuous material as the substrate **50**, the fin **52** and/or the substrate **50** may comprise a single material or a plurality of materials. In this context, the fin **52** refers to the portion extending between the neighboring isolation regions **56**.

[0012] A gate dielectric layer **92** is along sidewalls and over a top surface of the fin **52**, and a gate electrode **94** is over the gate dielectric layer **92**. Source/drain regions **82** are disposed in opposite sides of the fin **52** with respect to the gate dielectric layer **92** and gate electrode **94**. FIG. **1** further illustrates reference cross-sections that are used in later figures. Cross-section A-A is along a longitudinal axis of the gate electrode **94** and in a direction, for example, perpendicular to the direction of current flow between the source/drain regions **82** of the FinFET. Cross-section B-B is perpendicular to cross-section A-A and is along a longitudinal axis of the fin **52** and in a direction of, for example, a current flow between the source/drain regions **82** of the FinFET. Cross-section C-C is parallel to cross-section A-A and extends through a source/drain region of the FinFET. Subsequent figures refer to these reference cross-sections for clarity.

[0013] Some embodiments discussed herein are discussed in the context of FinFETs formed using a gate-last process. In other embodiments, a gate-first process may be used. Also, some embodiments contemplate aspects used in planar devices, such as planar FETs, nanostructure (e.g., nanosheet, nanowire, gate-all-around, or the like) field effect transistors (NSFETs), or the like.

[0014] FIGS. **2** through **18B** are cross-sectional views of intermediate stages in the manufacturing of FinFETs, in accordance with some embodiments. FIGS. **2** through **7** illustrate reference cross-section A-A illustrated in FIG. **1**, except for multiple fins/FinFETs. FIGS. **8A**, **9A**, **10A**, **11A**, **12A**, **13A**, **14A**, **17A**, and **18A** are illustrated along reference cross-section A-A illustrated in FIG. **1**, and FIGS. **8B**, **9B**, **10B**, **11B**, **12B**, **13B**, **14B**, **14C**, **15A**, **15B**, **15C**, **15D**, **17B**, and **18B** are illustrated along a similar cross-section B-B illustrated in FIG. **1**, except for multiple fins/FinFETs. FIGS. **10C** and **10D** are illustrated along reference cross-section C-C illustrated in FIG. **1**, except for multiple fins/FinFETs.

[0015] In FIG. 2, a substrate **50** is provided. The substrate **50** may be a semiconductor substrate, such as a bulk semiconductor, a semiconductor-on-insulator (SOI) substrate, or the like, which may be doped (e.g., with a p-type or an n-type dopant) or undoped. The substrate **50** may be a wafer, such as a silicon wafer. Generally, an SOI substrate is a layer of a semiconductor material formed on an insulator layer. The insulator layer may be, for example, a buried oxide (BOX) layer, a silicon oxide layer, or the like. The insulator layer is provided on a substrate, typically a silicon or glass substrate. Other substrates, such as a multi-layered or gradient substrate may also be used. In some embodiments, the semiconductor material of the substrate **50** may include silicon; germanium; a compound semiconductor including silicon carbide, gallium arsenide, gallium phosphide, indium phosphide, indium arsenide, and/or indium antimonide; an alloy semiconductor including silicon-germanium, gallium arsenide phosphide, aluminum indium arsenide, aluminum gallium arsenide, gallium indium arsenide, gallium indium phosphide, and/or gallium indium arsenide phosphide; or combinations thereof.

[0016] The substrate **50** has an n-type region **50N** and a p-type region **50P**. The n-type region **50N** can be for forming n-type devices, such as NMOS transistors, e.g., n-type FinFETs. The p-type region **50P** can be for forming p-type devices, such as PMOS transistors, e.g., p-type FinFETs. The n-type region **50N** may be physically separated from the p-type region **50P** (as illustrated by divider **51**), and any number of device features (e.g., other active devices, doped regions, isolation structures, etc.) may be disposed between the n-type region **50N** and the p-type region **50P**.

[0017] In FIG. 3, fins **52** are formed in the substrate **50**. The fins **52** are semiconductor strips. In some embodiments, the fins **52** may be formed in the substrate **50** by etching trenches in the substrate **50**. The etching may be any acceptable etch process, such as a reactive ion etch (RIE), neutral beam etch (NBE), the like, or a combination thereof. The etch may be anisotropic.

[0018] The fins may be patterned by any suitable method. For example, the fins **52** may be patterned using one or more photolithography processes, including double-patterning or multi-patterning processes. Generally, double-patterning or multi-patterning processes combine photolithography and self-aligned processes, allowing patterns to be created that have, for example, pitches smaller than what is otherwise obtainable using a single, direct photolithography process. For example, in one embodiment, a sacrificial layer is formed over a substrate and patterned using a photolithography process. Spacers are formed alongside the patterned sacrificial layer using a self-aligned process. The sacrificial layer is then removed, and the remaining spacers may then be used to pattern the fins. In some embodiments, the mask (or other layer) may remain on the fins **52**.

[0019] In FIG. 4, an insulation material **54** is formed over the substrate **50** and between neighboring fins **52**. The insulation material **54** may be an oxide, such as silicon oxide, a nitride, the like, or a combination thereof, and may be formed by a high density plasma chemical vapor deposition (HDP-CVD), a flowable CVD (FCVD) (e.g., a CVD-based material deposition in a remote plasma system and post curing to make it convert to another material, such as an oxide), the like, or a combination thereof. Other insulation materials formed by any acceptable process may be used. In the illustrated embodiment, the insulation material **54** is silicon oxide formed by a FCVD process. An anneal process may be performed once the insulation material is formed. In an embodiment, the insulation material **54** is formed such that excess insulation material **54** covers the fins **52**. Although the insulation material **54** is illustrated as a single layer, some embodiments may utilize multiple layers. For example, in some embodiments a liner (not shown) may first be formed along a surface of the substrate **50** and the fins **52**. Thereafter, a fill material, such as those discussed above may be formed over the liner.

[0020] In FIG. 5, a removal process is applied to the insulation material **54** to remove excess insulation material **54** over the fins **52**. In some embodiments, a planarization process such as a chemical mechanical polish (CMP), an etch-back process, combinations thereof, or the like may be utilized. The planarization process exposes the fins **52** such that top surfaces of the fins **52** and the insulation material **54** are level after the planarization process is complete. In embodiments in

which a mask remains on the fins 52, the planarization process may expose the mask or remove the mask such that top surfaces of the mask or the fins 52, respectively, and the insulation material 54 are level after the planarization process is complete.

[0021] In FIG. 6, the insulation material 54 is recessed to form Shallow Trench Isolation (STI) regions 56. The insulation material 54 is recessed such that upper portions of fins 52 in the n-type region 50N and in the p-type region 50P protrude from between neighboring STI regions 56. Further, the top surfaces of the STI regions 56 may have a flat surface as illustrated, a convex surface, a concave surface (such as dishing), or a combination thereof. The top surfaces of the STI regions 56 may be formed flat, convex, and/or concave by an appropriate etch. The STI regions 56 may be recessed using an acceptable etching process, such as one that is selective to the material of the insulation material 54 (e.g., etches the material of the insulation material 54 at a faster rate than the material of the fins 52). For example, an oxide removal using, for example, dilute hydrofluoric (dHF) acid may be used.

[0022] The process described with respect to FIGS. 2 through 6 is just one example of how the fins 52 may be formed. In some embodiments, the fins may be formed by an epitaxial growth process. For example, a dielectric layer can be formed over a top surface of the substrate 50, and trenches can be etched through the dielectric layer to expose the underlying substrate 50. Homoepitaxial structures can be epitaxially grown in the trenches, and the dielectric layer can be recessed such that the homoepitaxial structures protrude from the dielectric layer to form fins. Additionally, in some embodiments, heteroepitaxial structures can be used for the fins 52. For example, the fins 52 in FIG. 5 can be recessed, and a material different from the fins 52 may be epitaxially grown over the recessed fins 52. In such embodiments, the fins 52 comprise the recessed material as well as the epitaxially grown material disposed over the recessed material. In an even further embodiment, a dielectric layer can be formed over a top surface of the substrate 50, and trenches can be etched through the dielectric layer. Heteroepitaxial structures can then be epitaxially grown in the trenches using a material different from the substrate 50, and the dielectric layer can be recessed such that the heteroepitaxial structures protrude from the dielectric layer to form the fins 52. In some embodiments where homoepitaxial or heteroepitaxial structures are epitaxially grown, the epitaxially grown materials may be in situ doped during growth, which may obviate prior and subsequent implantations although in situ and implantation doping may be used together.

[0023] Still further, it may be advantageous to epitaxially grow a material in n-type region 50N (e.g., an NMOS region) different from the material in p-type region 50P (e.g., a PMOS region). In various embodiments, upper portions of the fins 52 may be formed from silicon-germanium ($\text{Si.sub.xGe.sub.1-x}$, where x can be in the range of 0 to 1), silicon carbide, pure or substantially pure germanium, a III-V compound semiconductor, a II-VI compound semiconductor, or the like. For example, the available materials for forming III-V compound semiconductor include, but are not limited to, indium arsenide, aluminum arsenide, gallium arsenide, indium phosphide, gallium nitride, indium gallium arsenide, indium aluminum arsenide, gallium antimonide, aluminum antimonide, aluminum phosphide, gallium phosphide, and the like.

[0024] Further in FIG. 6, appropriate wells (not shown) may be formed in the fins 52 and/or the substrate 50. In some embodiments, a P well may be formed in the n-type region 50N, and an N well may be formed in the p-type region 50P. In some embodiments, a P well or an N well are formed in both the n-type region 50N and the p-type region 50P.

[0025] In the embodiments with different well types, the different implant steps for the n-type region 50N and the p-type region 50P may be achieved using a photoresist and/or other masks (not shown). For example, a photoresist may be formed over the fins 52 and the STI regions 56 in the n-type region 50N. The photoresist is patterned to expose the p-type region 50P of the substrate 50. The photoresist can be formed by using a spin-on technique and can be patterned using acceptable photolithography techniques. Once the photoresist is patterned, an n-type impurity implant is performed in the p-type region 50P, and the photoresist may act as a mask to substantially prevent

n-type impurities from being implanted into the n-type region **50N**. The n-type impurities may be phosphorus, arsenic, antimony, or the like implanted in the region to a concentration of equal to or less than 10^{18} cm.⁻³, such as between about 10^{16} cm.⁻³ and about 10^{18} cm.⁻³. After the implant, the photoresist is removed, such as by an acceptable ashing process. [0026] Following the implanting of the p-type region **50P**, a photoresist is formed over the fins **52** and the STI regions **56** in the p-type region **50P**. The photoresist is patterned to expose the n-type region **50N** of the substrate **50**. The photoresist can be formed by using a spin-on technique and can be patterned using acceptable photolithography techniques. Once the photoresist is patterned, a p-type impurity implant may be performed in the n-type region **50N**, and the photoresist may act as a mask to substantially prevent p-type impurities from being implanted into the p-type region **50P**. The p-type impurities may be boron, boron fluoride, indium, or the like implanted in the region to a concentration of equal to or less than 10^{18} cm.⁻³, such as between about 10^{16} cm.⁻³ and about 10^{18} cm.⁻³. After the implant, the photoresist may be removed, such as by an acceptable ashing process.

[0027] After the implants of the n-type region **50N** and the p-type region **50P**, an anneal may be performed to repair implant damage and to activate the p-type and/or n-type impurities that were implanted. In some embodiments, the grown materials of epitaxial fins may be in situ doped during growth, which may obviate the implantations, although in situ and implantation doping may be used together.

[0028] In FIG. 7, a dummy dielectric layer **60** is formed on the fins **52**. The dummy dielectric layer **60** may be, for example, silicon oxide, silicon nitride, a combination thereof, or the like, and may be deposited or thermally grown according to acceptable techniques. A dummy gate layer **62** is formed over the dummy dielectric layer **60**, and a mask layer **64** is formed over the dummy gate layer **62**. The dummy gate layer **62** may be deposited over the dummy dielectric layer **60** and then planarized, such as by a CMP. The mask layer **64** may be deposited over the dummy gate layer **62**. The dummy gate layer **62** may be a conductive or non-conductive material and may be selected from a group including amorphous silicon, polycrystalline-silicon (polysilicon), polycrystalline silicon-germanium (poly-SiGe), metallic nitrides, metallic silicides, metallic oxides, and metals. The dummy gate layer **62** may be deposited by physical vapor deposition (PVD), CVD, sputter deposition, or other techniques for depositing the selected material. The dummy gate layer **62** may be made of other materials that have a high etching selectivity from the etching of isolation regions, e.g., the STI regions **56** and/or the dummy dielectric layer **60**. The mask layer **64** may include one or more layers of, for example, silicon nitride, silicon oxynitride, or the like. In this example, a single dummy gate layer **62** and a single mask layer **64** are formed across the n-type region **50N** and the p-type region **50P**. It is noted that the dummy dielectric layer **60** is shown covering only the fins **52** for illustrative purposes only. In some embodiments, the dummy dielectric layer **60** may be deposited such that the dummy dielectric layer **60** covers the STI regions **56**, extending over the STI regions and between the dummy gate layer **62** and the STI regions.

[0029] FIGS. 8A through 16B illustrate various additional steps in the manufacturing of embodiment devices. FIGS. 8A through 16B illustrate features in either of the n-type region **50N** and the p-type region **50P**. For example, the structures illustrated in FIGS. 8A through 16B may be applicable to both the n-type region **50N** and the p-type region **50P**. Differences (if any) in the structures of the n-type region **50N** and the p-type region **50P** are described in the text accompanying each figure.

[0030] In FIGS. 8A and 8B, the mask layer **64** (see FIG. 7) may be patterned using acceptable photolithography and etching techniques to form masks **74**. The pattern of the masks **74** then may be transferred to the dummy gate layer **62**. In some embodiments (not illustrated), the pattern of the masks **74** may also be transferred to the dummy dielectric layer **60** by an acceptable etching technique to form dummy gates **72**. The dummy gates **72** cover respective channel regions **58** of the fins **52**. The pattern of the masks **74** may be used to physically separate each of the dummy

gates **72** from adjacent dummy gates. The dummy gates **72** may also have a lengthwise direction substantially perpendicular to the lengthwise direction of respective epitaxial fins **52**.

[0031] Further in FIGS. **8A** and **8B**, gate seal spacers **80** can be formed on exposed surfaces of the dummy gates **72**, the masks **74**, and/or the fins **52**. A thermal oxidation or a deposition followed by an anisotropic etch may form the gate seal spacers **80**. The gate seal spacers **80** may be formed of silicon oxide, silicon nitride, silicon oxynitride, or the like.

[0032] After the formation of the gate seal spacers **80**, implants for lightly doped source/drain (LDD) regions (not explicitly illustrated) may be performed. In the embodiments with different device types, similar to the implants discussed above in FIG. **6**, a mask, such as a photoresist, may be formed over the n-type region **50N**, while exposing the p-type region **50P**, and appropriate type (e.g., p-type) impurities may be implanted into the exposed fins **52** in the p-type region **50P**. The mask may then be removed. Subsequently, a mask, such as a photoresist, may be formed over the p-type region **50P** while exposing the n-type region **50N**, and appropriate type impurities (e.g., n-type) may be implanted into the exposed fins **52** in the n-type region **50N**. The mask may then be removed. The n-type impurities may be the any of the n-type impurities previously discussed, and the p-type impurities may be the any of the p-type impurities previously discussed. The lightly doped source/drain regions may have a concentration of impurities of from about 10^{15} cm.^{sup.}−3 to about 10^{19} cm.^{sup.}−3. An anneal may be used to repair implant damage and to activate the implanted impurities.

[0033] In FIGS. **9A** and **9B**, gate spacers **86** are formed on the gate seal spacers **80** along sidewalls of the dummy gates **72** and the masks **74**. The gate spacers **86** may be formed by conformally depositing an insulating material and subsequently anisotropically etching the insulating material. The insulating material of the gate spacers **86** may be silicon oxide, silicon nitride, silicon oxynitride, silicon carbonitride, a combination thereof, or the like.

[0034] It is noted that the above disclosure generally describes a process of forming spacers and LDD regions. Other processes and sequences may be used. For example, fewer or additional spacers may be utilized, different sequence of steps may be utilized (e.g., the gate seal spacers **80** may not be etched prior to forming the gate spacers **86**, yielding “L-shaped” gate seal spacers, spacers may be formed and removed, and/or the like. Furthermore, the n-type and p-type devices may be formed using a different structures and steps. For example, LDD regions for n-type devices may be formed prior to forming the gate seal spacers **80** while the LDD regions for p-type devices may be formed after forming the gate seal spacers **80**.

[0035] In FIGS. **10A** and **10B** epitaxial source/drain regions **82** are formed in the fins **52**. The epitaxial source/drain regions **82** are formed in the fins **52** such that each dummy gate **72** is disposed between respective neighboring pairs of the epitaxial source/drain regions **82**. In some embodiments the epitaxial source/drain regions **82** may extend into, and may also penetrate through, the fins **52**. In some embodiments, the gate spacers **86** are used to separate the epitaxial source/drain regions **82** from the dummy gates **72** by an appropriate lateral distance so that the epitaxial source/drain regions **82** do not short out subsequently formed gates of the resulting FinFETs. A material of the epitaxial source/drain regions **82** may be selected to exert stress in the respective channel regions **58**, thereby improving performance.

[0036] The epitaxial source/drain regions **82** in the n-type region **50N** may be formed by masking the p-type region **50P** and etching source/drain regions of the fins **52** in the n-type region **50N** to form recesses in the fins **52**. Then, the epitaxial source/drain regions **82** in the n-type region **50N** are epitaxially grown in the recesses. The epitaxial source/drain regions **82** may include any acceptable material, such as appropriate for n-type FinFETs. For example, if the fin **52** is silicon, the epitaxial source/drain regions **82** in the n-type region **50N** may include materials exerting a tensile strain in the channel region **58**, such as silicon, silicon carbide, phosphorous doped silicon carbide, silicon phosphide, or the like. The epitaxial source/drain regions **82** in the n-type region **50N** may have surfaces raised from respective surfaces of the fins **52** and may have facets.

[0037] The epitaxial source/drain regions **82** in the p-type region **50P** may be formed by masking the n-type region **50N** and etching source/drain regions of the fins **52** in the p-type region **50P** to form recesses in the fins **52**. Then, the epitaxial source/drain regions **82** in the p-type region **50P** are epitaxially grown in the recesses. The epitaxial source/drain regions **82** may include any acceptable material, such as appropriate for p-type FinFETs. For example, if the fin **52** is silicon, the epitaxial source/drain regions **82** in the p-type region **50P** may comprise materials exerting a compressive strain in the channel region **58**, such as silicon-germanium, boron doped silicon-germanium, germanium, germanium tin, or the like. The epitaxial source/drain regions **82** in the p-type region **50P** may have surfaces raised from respective surfaces of the fins **52** and may have facets.

[0038] The epitaxial source/drain regions **82** and/or the fins **52** may be implanted with dopants to form source/drain regions, similar to the process previously discussed for forming lightly-doped source/drain regions, followed by an anneal. The source/drain regions may have an impurity concentration of between about 10^{19} cm.⁻³ and about 10^{21} cm.⁻³. The n-type and/or p-type impurities for source/drain regions may be any of the impurities previously discussed. In some embodiments, the epitaxial source/drain regions **82** may be in situ doped during growth.

[0039] As a result of the epitaxy processes used to form the epitaxial source/drain regions **82** in the n-type region **50N** and the p-type region **50P**, upper surfaces of the epitaxial source/drain regions have facets which expand laterally outward beyond sidewalls of the fins **52**. In some embodiments, these facets cause adjacent source/drain regions **82** of a same FinFET to merge as illustrated by FIG. **10C**. In other embodiments, adjacent source/drain regions **82** remain separated after the epitaxy process is completed as illustrated by FIG. **10D**. In the embodiments illustrated in FIGS. **10C** and **10D**, gate spacers **86** are formed covering a portion of the sidewalls of the fins **52** that extend above the STI regions **56** thereby blocking the epitaxial growth. In some other embodiments, the spacer etch used to form the gate spacers **86** may be adjusted to remove the spacer material to allow the epitaxially grown region to extend to the surface of the STI region **56**.

[0040] In FIGS. **11A** and **11B**, a first interlayer dielectric (ILD) **88** is deposited over the structure illustrated in FIGS. **10A** and **10B**. The first ILD **88** may be formed of a dielectric material, and may be deposited by any suitable method, such as CVD, plasma-enhanced CVD (PECVD), or FCVD. Dielectric materials may include phospho-silicate glass (PSG), boro-silicate glass (BSG), boron-doped phospho-silicate glass (BPSG), undoped silicate glass (USG), or the like. Other insulation materials formed by any acceptable process may be used. In some embodiments, a contact etch stop layer (CESL) **87** is disposed between the first ILD **88** and the epitaxial source/drain regions **82**, the masks **74**, and the gate spacers **86**. The CESL **87** may comprise a dielectric material, such as, silicon nitride, silicon oxide, silicon oxynitride, or the like, having a lower etch rate than the material of the overlying first ILD **88**.

[0041] In FIGS. **12A** and **12B**, a planarization process, such as a CMP, may be performed to level the top surface of the first ILD **88** with the top surfaces of the dummy gates **72** or the masks **74**. The planarization process may also remove the masks **74** on the dummy gates **72**, and portions of the gate seal spacers **80** and the gate spacers **86** along sidewalls of the masks **74**. After the planarization process, top surfaces of the dummy gates **72**, the gate seal spacers **80**, the gate spacers **86**, and the first ILD **88** are level. Accordingly, the top surfaces of the dummy gates **72** are exposed through the first ILD **88**. In some embodiments, the masks **74** may remain, in which case the planarization process levels the top surface of the first ILD **88** with the top surfaces of the top surface of the masks **74**.

[0042] In FIGS. **13A** and **13B**, the dummy gates **72**, and the masks **74** if present, are removed in an etching step(s), so that recesses **90** are formed. Portions of the dummy dielectric layer **60** in the recesses **90** may also be removed. In some embodiments, only the dummy gates **72** are removed and the dummy dielectric layer **60** remains and is exposed by the recesses **90**. In some embodiments, the dummy dielectric layer **60** is removed from recesses **90** in a first region of a die

(e.g., a core logic region) and remains in recesses **90** in a second region of the die (e.g., an input/output region). In some embodiments, the dummy gates **72** are removed by an anisotropic dry etch process. For example, the etching process may include a dry etch process using reaction gas(es) that selectively etch the dummy gates **72** with little or no etching of the first ILD **88** or the gate spacers **86**. Each recess **90** exposes and/or overlies a channel region **58** of a respective fin **52**. Each channel region **58** is disposed between neighboring pairs of the epitaxial source/drain regions **82**. During the removal, the dummy dielectric layer **60** may be used as an etch stop layer when the dummy gates **72** are etched. The dummy dielectric layer **60** may then be optionally removed after the removal of the dummy gates **72**.

[0043] In FIGS. **14A** and **14B**, gate dielectric layers **92** and gate electrodes **94** are formed for replacement gates. FIG. **14C** illustrates a detailed view of region **89** of FIG. **14B**. Gate dielectric layers **92** may be one or more layers deposited in the recesses **90**, such as on the top surfaces and the sidewalls of the fins **52** and on sidewalls of the gate seal spacers **80**/gate spacers **86**. The gate dielectric layers **92** may also be formed on the top surface of the first ILD **88**. In some embodiments, the gate dielectric layers **92** comprise one or more dielectric layers, such as one or more layers of silicon oxide, silicon nitride, metal oxide, metal silicate, or the like. For example, in some embodiments, the gate dielectric layers **92** include an interfacial layer **92A**, e.g., of silicon oxide formed by thermal or chemical oxidation, and an overlying high-k dielectric material **92B**, such as a metal oxide or a silicate of hafnium, aluminum, zirconium, lanthanum, manganese, barium, titanium, lead, and combinations thereof. The gate dielectric layers **92** may include a dielectric layer having a k value greater than about 7.0. The formation methods of the gate dielectric layers **92** may include Molecular-Beam Deposition (MBD), ALD, PECVD, and the like. In embodiments where portions of the dummy gate dielectric **60** remain in the recesses **90**, the gate dielectric layers **92** include a material of the dummy gate dielectric **60** (e.g., SiO₂).

[0044] The gate electrodes **94** are deposited over the gate dielectric layers **92** and fill the remaining portions of the recesses **90**. The gate electrodes **94** may include a metal-containing material such as titanium nitride, titanium oxide, titanium carbo-nitride, tantalum nitride, tantalum carbide, tantalum carbo-nitride, titanium aluminum, cobalt, ruthenium, aluminum, tungsten, combinations thereof, or multi-layers thereof. For example, although a single layer gate electrode **94** is illustrated in FIG. **14B**, the gate electrode **94** may comprise any number of p-type work function tuning layers **94A**, any number of n-type work function tuning layers **94B**, one or more glue layers **94C**, and a fill material **94D** as illustrated by FIG. **14C**. In the n-type region **50N**, the p-type work function tuning layers **94A** may be removed prior to depositing the n-type work function tuning layer(s) **94B**. After the filling of the recesses **90**, a planarization process, such as a CMP, may be performed to remove the excess portions of the gate dielectric layers **92** and the material of the gate electrodes **94**, which excess portions are over the top surface of the ILD **88**. The remaining portions of material of the gate electrodes **94** and the gate dielectric layers **92** thus form replacement gates of the resulting FinFETs. The gate electrodes **94** and the gate dielectric layers **92** may be collectively referred to as a “gate stack.” The gate and the gate stacks may extend along sidewalls of a channel region **58** of the fins **52**.

[0045] The formation of the gate dielectric layers **92** in the n-type region **50N** and the p-type region **50P** may occur simultaneously such that the gate dielectric layers **92** in each region are formed from the same materials, and the formation of the gate electrodes **94** may occur simultaneously such that the gate electrodes **94** in each region are formed from the same materials. In some embodiments, the liner layer **94A** may be removed from the n-type region **50N** prior to depositing the work function tuning layer(s) **94B**. In some embodiments, the gate dielectric layers **92** in each region may be formed by distinct processes, such that the gate dielectric layers **92** may be different materials, and/or the gate electrodes **94** in each region may be formed by distinct processes, such that the gate electrodes **94** may be different materials. Various masking steps may be used to mask and expose appropriate regions when using distinct processes.

[0046] FIGS. 15A through 15D illustrate cross-sectional views of forming the gate electrodes **94** according to some embodiments. For ease of illustration, only a detailed view of the gate electrode (e.g., similar to the region **89** of FIGS. 14B and 14C) is illustrated for the p-type region **50P** and the n-type region **50N**.

[0047] In FIG. 15A, a p-type work function tuning layer **94A** is deposited in the recesses **90** in the p-type region **50P** and the n-type region **50N**. In some embodiments, the p-type work function tuning layer **94A** comprises titanium carbon nitride (Ti—C—N), which is formed using an ALD process. FIG. 16A illustrates process flow of an embodiment ALD process **200** when the p-type work function tuning layer **94A** comprises Ti—C—N. The ALD process **200** may include deposition loops **202**, **204**, and **206**, all of which are performed in a single process (e.g., in-situ within a same process chamber and without breaking vacuum). Each of the deposition loops **202**, **204**, and **206** may deposit at a rate in a range of 0.2 Å/loop to 8 Å/loop. In some embodiments, the ALD process **200** may be performed at a temperature in a range of 200° C. to 600° C. at a pressure of 0.5 Torr to 50 Torr.

[0048] The ALD process **200** begins with one or more deposition loops **202** to deposit one or more monolayers of a titanium nitride. Each deposition loop **202** includes pulsing a first titanium-comprising precursor (e.g., TiCl.sub.4, or the like) into the ALD chamber, purging the ALD chamber, pulsing a second nitrogen-comprising precursor (e.g., NH.sub.3) into the ALD chamber, and purging the ALD chamber. The titanium-comprising precursor reacts with the nitrogen-comprising precursor to deposit a monolayer of titanium nitride on exposed surfaces of the recesses **90**. Each deposition loop **202** deposits a single monolayer of titanium nitride, and any number of deposition loops **202** may be performed to deposit a desired quantity of titanium nitride monolayers.

[0049] The ALD process **200** continues one or more deposition loops **204** to deposit one or more monolayers of a titanium carbide. Each deposition loop **204** includes pulsing the first titanium-comprising precursor (e.g., TiCl.sub.4, or the like) into the ALD chamber, purging the ALD chamber, pulsing a third carbon-comprising precursor (e.g., trimethylaluminum (TMA), aluminum triethyl (TEA), or the like) into the ALD chamber, and purging the ALD chamber. The titanium-comprising precursor reacts with the carbon-comprising precursor to deposit a monolayer of titanium carbide on exposed surfaces of the recesses **90**. Each deposition loop **204** deposits a single monolayer of titanium carbide, and any number of deposition loops **204** may be performed to deposit a desired quantity of titanium carbide monolayers.

[0050] Subsequently, the ALD process **200** continues with one or more deposition loops **206** to deposit one or more additional monolayers of a titanium nitride. Each deposition loop **206** includes pulsing the first titanium-comprising precursor (e.g., TiCl.sub.4, or the like) into the ALD chamber, purging the ALD chamber, pulsing the second nitrogen-comprising precursor (e.g., NH.sub.3) into the ALD chamber, and purging the ALD chamber. Similar to the deposition loops **202**, the titanium-comprising precursor reacts with the nitrogen-comprising precursor to deposit a monolayer of titanium nitride on exposed surfaces of the recesses **90**. Each deposition loop **206** deposits a single monolayer of titanium nitride, and any number of deposition loops **206** may be performed to deposit a desired quantity of titanium nitride monolayers over the titanium carbide monolayers.

[0051] Alternatively, in some embodiments, the p-type work function tuning layer **94A** comprises tantalum carbon nitride (Ta—C—N), which is formed using an ALD process. FIG. 16B illustrates process flow of an embodiment ALD process **210** when the p-type work function tuning layer **94A** comprises Ta—C—N. The ALD process **210** may include deposition loops **212**, **214**, and **216**, all of which are performed in a single process (e.g., in-situ within a same process chamber and without breaking vacuum). Each of the deposition loops **212**, **214**, and **216** may deposit at a rate in a range of 0.2 Å/loop to 8 Å/loop. In some embodiments, the ALD process **210** may be performed at a temperature in a range of 200° C. to 600° C. at a pressure of 0.5 Torr to 50 Torr.

[0052] The ALD process **210** begins with one or more deposition loops **212** to deposit one or more monolayers of a tantalum nitride. Each deposition loop **202** includes pulsing a fourth tantalum-comprising precursor (e.g., TaCl.sub.5, or the like) into the ALD chamber, purging the ALD chamber, pulsing the second nitrogen-comprising precursor (e.g., NH.sub.3) into the ALD chamber, and purging the ALD chamber. The tantalum-comprising precursor reacts with the nitrogen-comprising precursor to deposit a monolayer of tantalum nitride on exposed surfaces of the recesses **90**. Each deposition loop **212** deposits a single monolayer of tantalum nitride, and any number of deposition loops **212** may be performed to deposit a desired quantity of tantalum nitride monolayers.

[0053] The ALD process **210** continues one or more deposition loops **214** to deposit one or more monolayers of a tantalum carbide. Each deposition loop **214** includes pulsing the fourth tantalum-comprising precursor (e.g., TaCl.sub.5, or the like) into the ALD chamber, purging the ALD chamber, pulsing the third carbon-comprising precursor (e.g., TMA, TEA, or the like) into the ALD chamber, and purging the ALD chamber. The tantalum-comprising precursor reacts with the carbon-comprising precursor to deposit a monolayer of titanium carbide on exposed surfaces of the recesses **90**. Each deposition loop **214** deposits a single monolayer of tantalum carbide, and any number of deposition loops **214** may be performed to deposit a desired quantity of tantalum carbide monolayers.

[0054] Subsequently, the ALD process **210** continues with one or more deposition loops **216** to deposit one or more additional monolayers of a tantalum nitride. Each deposition loop **216** includes pulsing the fourth tantalum-comprising precursor (e.g., TaCl.sub.5, or the like) into the ALD chamber, purging the ALD chamber, pulsing the second nitrogen-comprising precursor (e.g., NH.sub.3) into the ALD chamber, and purging the ALD chamber. Similar to the deposition loops **212**, the tantalum-comprising precursor reacts with the nitrogen-comprising precursor to deposit a monolayer of tantalum nitride on exposed surfaces of the recesses **90**. Each deposition loop **216** deposits a single monolayer of tantalum nitride, and any number of deposition loops **216** may be performed to deposit a desired quantity of tantalum nitride monolayers over the tantalum carbide monolayers.

[0055] By adjusting the quantity of carbide deposition loops in the ALD process (e.g., loops **204** or **214** described above) and/or adjusting the quantity of nitrogen deposition loops in the ALD process (e.g., loops **202**, **206**, **212**, and/or **216** described above), a ratio of carbon to nitrogen in the p-type work function tuning layer **94A** can be adjusted such that a desired work function is achieved. For example, by increasing the number of carbide deposition loops in the ALD process, the ratio of carbon to nitrogen in the p-type work function tuning layer **94A** can be increased. By depositing the p-type work function tuning layer **94A** to have a relatively high ratio of carbon to nitrogen, a lower work function (e.g., more n-type) can be achieved. Further, by depositing the p-type work function tuning layer **94A** to have a relatively low ratio of carbon to nitrogen, a higher work function (e.g., more p-type) can be achieved. In some embodiments, a ratio of carbon to nitrogen in the p-type work function tuning layer **94A** is in a range of 0.05 to 0.95. In some embodiments, the ratio of carbon to nitrogen in the p-type work function tuning layer **94A** is in a range of 0.05 to 0.55, which allows for precise tuning of work functions (and associated threshold voltages) of various transistors of the device. Thus, various embodiments provide a method for tuning a work function of a p-type work function tuning layer with improved precision.

[0056] Further, although only one p-type work function tuning layer is illustrated, it should be understood that some embodiments may include a semiconductor device having a first gate electrode and a second gate electrode with different p-type work function tuning layers. For example, the first gate electrode may include a first p-type work function tuning layer with a first carbon to nitrogen ratio, and the second gate electrode may include a second p-type work function tuning layer with a second carbon to nitrogen ratio. The first carbon to nitrogen ratio may be different than the second carbon to nitrogen ratio. The first and second p-type work function tuning

layers may be selectively formed, for example, by masking recesses for each of the first and second gate electrodes as appropriate during deposition and/or etching of the first and/or second p-type work function tuning layers. In this manner, different types of gate electrodes may be formed with different p-type work function tuning layers, different work functions, and different threshold voltages based on circuit design. For example, in some embodiments, the first carbon to nitrogen ratio may be higher than the second carbon to nitrogen ratio, and as a result the first gate electrode may have a lower work function (e.g., a lower threshold voltage) than the second gate electrode.

[0057] Referring to FIG. 15B, the processing may continue by removing the p-type work function tuning layer **94A** from the recesses **90** in the n-type region **50N** while leaving the p-type work function tuning layer **94A** in the recesses **90** in the p-type region **50P**. In some embodiments, the selective removal of the p-type work function tuning layer **94A** from the n-type regions **50N** may be achieved by masking the p-type work function tuning layer **94A** in the p-type region **50P**. For example, a mask (e.g., a back side anti-reflective (BARC) layer) may be deposited in the recesses **90** in the p-type region **50P** to cover the p-type work function tuning layer **94A** while an etching process is performed to remove the p-type work function tuning layer **94A** from the n-type region **50N**. After the etching process, the mask may then be removed.

[0058] In FIG. 15C, an n-type work function tuning layer **94B** is then formed conformally in the recesses **90** in the n-type region **50N** and the p-type region **50P**. Further, the n-type work function tuning layer **94B** may be deposited over the p-type work function tuning layer **94C** in the p-type region **50P**. The n-type work function tuning layer **94B** may be any acceptable material to tune a work function of a device to a desired amount given the application of the device to be formed, and may be deposited using any acceptable deposition process. In some embodiments, the n-type work function tuning layer **94B** may comprise aluminum (Al), aluminum nitride (AlN), titanium aluminum (TiAl), tantalum aluminum (TaAl), or the like deposited by ALD, CVD, PVD, or the like.

[0059] In FIG. 15D, an adhesion or glue layer **94C** is formed conformally on the n-type work function tuning layer **94B** in the n-type region **50N** and the p-type region **50P**. The glue layer **116** may comprise titanium nitride (TiN) or the like deposited by ALD or the like. Also in FIG. 15D, a conductive material **94D** is deposited on the glue layer **94C**. The conductive material **94D** can include a metal, such as tungsten (W), aluminum (Al), cobalt (Co), ruthenium (Ru), combinations thereof or the like. The conductive material **94D** can be deposited using CVD, PVD, the like, or a combination thereof. The conductive material **94D** fills the remaining portions of the recesses **90**.

[0060] After the conductive material **94D** is deposited, a planarization process, such as a CMP, may be performed to remove the excess portions of gate dielectrics **92**, the p-type work function tuning layer **94A**, the n-type work function tuning layer **94B**, the glue layer **94C**, and the conductive material **94D**, which excess portions are over the top surface of ILD **90**, to form the gate dielectrics **92** and gate electrodes **94**.

[0061] In FIGS. 15A and 15B, a gate mask **96** is formed over the gate stack (including a gate dielectric layer **92** and a corresponding gate electrode **94**), and the gate mask may be disposed between opposing portions of the gate spacers **86**. In some embodiments, forming the gate mask **96** includes recessing the gate stack so that a recess is formed directly over the gate stack and between opposing portions of gate spacers **86**. A gate mask **96** comprising one or more layers of dielectric material, such as silicon nitride, silicon oxynitride, or the like, is filled in the recess, followed by a planarization process to remove excess portions of the dielectric material extending over the first ILD **88**.

[0062] As also illustrated in FIGS. 17A and 17B, a second ILD **108** is deposited over the first ILD **88**. In some embodiments, the second ILD **108** is a flowable film formed by a flowable CVD method. In some embodiments, the second ILD **108** is formed of a dielectric material such as PSG, BSG, BPSG, USG, or the like, and may be deposited by any suitable method, such as CVD and PECVD. The subsequently formed gate contacts **110** (FIGS. 18A and 18B) penetrate through the

second ILD **108** and the gate mask **96** to contact the top surface of the recessed gate electrode **94**. [0063] In FIGS. **18A** and **18B**, gate contacts **110** and source/drain contacts **112** are formed through the second ILD **108** and the first ILD **88** in accordance with some embodiments. Openings for the source/drain contacts **112** are formed through the first and second ILDs **88** and **108**, and openings for the gate contact **110** are formed through the second ILD **108** and the gate mask **96**. The openings may be formed using acceptable photolithography and etching techniques. A liner (not shown), such as a diffusion barrier layer, an adhesion layer, or the like, and a conductive material are formed in the openings. The liner may include titanium, titanium nitride, tantalum, tantalum nitride, or the like. The conductive material may be copper, a copper alloy, silver, gold, tungsten, cobalt, aluminum, nickel, or the like. A planarization process, such as a CMP, may be performed to remove excess material from a surface of the ILD **108**. The remaining liner and conductive material form the source/drain contacts **112** and gate contacts **110** in the openings. An anneal process may be performed to form a silicide at the interface between the epitaxial source/drain regions **82** and the source/drain contacts **112**. The source/drain contacts **112** are physically and electrically coupled to the epitaxial source/drain regions **82**, and the gate contacts **110** are physically and electrically coupled to the gate electrodes **106**. The source/drain contacts **112** and gate contacts **110** may be formed in different processes, or may be formed in the same process. Although shown as being formed in the same cross-sections, it should be appreciated that each of the source/drain contacts **112** and gate contacts **110** may be formed in different cross-sections, which may avoid shorting of the contacts.

[0064] The disclosed FinFET embodiments could also be applied to nanostructure devices such as nanostructure (e.g., nanosheet, nanowire, gate-all-around, or the like) field effect transistors (NSFETs). In an NSFET embodiment, the fins are replaced by nanostructures formed by patterning a stack of alternating layers of channel layers and sacrificial layers. Dummy gate stacks and source/drain regions are formed in a manner similar to the above-described embodiments. After the dummy gate stacks are removed, the sacrificial layers can be partially or fully removed in channel regions. The replacement gate structures are formed in a manner similar to the above-described embodiments, the replacement gate structures may partially or completely fill openings left by removing the sacrificial layers, and the replacement gate structures may partially or completely surround the channel layers in the channel regions of the NSFET devices. ILDs and contacts to the replacement gate structures and the source/drain regions may be formed in a manner similar to the above-described embodiments. A nanostructure device can be formed as disclosed in U.S. Patent Application Publication No. 2016/0365414, which is incorporated herein by reference in its entirety.

[0065] Various embodiments provide a method of depositing a WFM layer of a gate electrode for improved work function tuning. In some embodiments, the WFM layer is a p-type layer that is formed by an ALD process. The ALD process may deposit a combination of nitride monolayers (e.g., titanium nitride, tantalum nitride, or the like) and carbide monolayers (e.g., titanium carbide, tantalum carbide, or the like). By adjusting the ratio of a quantity of carbide monolayers to a quantity of nitride monolayers that are deposited, a work function of the gate electrode can be more precisely tuned. For example, a higher ratio carbon to nitrogen in the WFM layer may result in the WFM layer having a lower work function (e.g., more n-type), and a lower ratio of carbon to nitrogen in the WFM layer may result in the WFM layer having a higher work function (e.g., more p-type).

[0066] In some embodiments, a method for forming a gate electrode includes depositing a first work function tuning layer over a gate dielectric layer using an atomic layer deposition process, wherein the atomic layer deposition process comprises: depositing one or more first nitride monolayers; and depositing one or more carbide monolayers over the one or more first nitride monolayers; depositing an adhesion layer of the first work function tuning layer; and depositing a conductive material over the adhesion layer. Optionally, in some embodiments, depositing the one

or more first nitride monolayers comprises: pulsing a metal-comprising precursor in a deposition chamber where the atomic layer deposition process is performed; and pulsing a nitrogen-comprising precursor in the deposition chamber. Optionally, in some embodiments, the metal-comprising precursor is TiCl_4 , and the nitrogen-comprising precursor is NH_3 . Optionally, in some embodiments, the metal-comprising precursor is TaCl_5 , and the nitrogen-comprising precursor is NH_3 . Optionally, in some embodiments, depositing the one or more carbide monolayers comprises: pulsing a metal-comprising precursor in a deposition chamber where the atomic layer deposition process is performed; and pulsing a carbon-comprising precursor in the deposition chamber. Optionally, in some embodiments, the metal-comprising precursor is TiCl_4 , and wherein the carbon-comprising precursor is trimethylaluminum (TMA) or aluminum triethyl (TEA). Optionally, in some embodiments, the metal-comprising precursor is TaCl_5 , and wherein the carbon-comprising precursor is trimethylaluminum (TMA) or aluminum triethyl (TEA). Optionally, in some embodiments, the atomic layer deposition process further comprises depositing one or more second nitride monolayers over the one or more carbide monolayers. Optionally, in some embodiments, the method further comprises prior to depositing the adhesion layer, depositing a second work function tuning layer on the first work function tuning layer. Optionally, in some embodiments, the first work function tuning layer is a p-type layer, and wherein the second work function tuning layer is an n-type layer.

[0067] In some embodiments, a method includes: forming a first recess between first gate spacers; depositing a p-type work function tuning layer in the first recess, wherein depositing the p-type work function tuning layer comprises: depositing first monolayers of a nitride; depositing second monolayers of a carbide over the first monolayers; and depositing third monolayers of the nitride over the second monolayers; depositing an n-type work function tuning layer in the first recess over the p-type work function tuning layer; depositing an adhesion layer in the first recess over the n-type work function tuning layer; and depositing a conductive fill material in the first recess over the adhesion layer. Optionally, in some embodiments, depositing the first monolayers and depositing the third monolayers comprises depositing tantalum-comprising monolayers. Optionally, in some embodiments, depositing the first monolayers and depositing the third monolayers comprises depositing titanium-comprising monolayers. Optionally, in some embodiments, the method further includes forming a second recess between second gate spacers; depositing the p-type work function tuning layer in the second recess; removing first portions of the p-type work function tuning layer from the second recess while masking second portions of the p-type work function tuning layer in the first recess; after removing the first portions of the p-type work function tuning layer, depositing the n-type work function tuning layer in the second recess; depositing the adhesion layer in the second recess over the n-type work function tuning layer; and depositing the conductive fill material in the second recess over the adhesion layer. Optionally, in some embodiments, depositing the second monolayers comprises flowing a carbon-comprising precursor, and wherein the carbon-comprising precursor is trimethylaluminum (TMA) or aluminum triethyl (TEA).

[0068] In some embodiments, a device includes a first source/drain region; a second source/drain region; and a first gate between the first source/drain region and the second source/drain region, the first gate comprising: a gate dielectric; and a gate electrode over the gate dielectric, the gate electrode comprising: a first p-type work function tuning metal over the gate dielectric, the first p-type work function tuning metal comprising carbon and nitrogen; an adhesive layer over the first p-type work function tuning metal; and a fill metal over the adhesive layer. Optionally, in some embodiments, the first p-type work function tuning metal further comprises titanium. Optionally, in some embodiments, the first p-type work function tuning metal further comprises tantalum. Optionally, in some embodiments, the device further includes an n-type work function tuning metal between the first p-type work function tuning metal and the adhesive layer. Optionally, in some embodiments, a ratio of carbon to nitrogen in the first p-type work function tuning metal is in a range of 0.05 to 0.55.

[0069] The foregoing outlines features of several embodiments so that those skilled in the art may better understand the aspects of the present disclosure. Those skilled in the art should appreciate that they may readily use the present disclosure as a basis for designing or modifying other processes and structures for carrying out the same purposes and/or achieving the same advantages of the embodiments introduced herein. Those skilled in the art should also realize that such equivalent constructions do not depart from the spirit and scope of the present disclosure, and that they may make various changes, substitutions, and alterations herein without departing from the spirit and scope of the present disclosure.

Claims

1. A method comprising: removing a dummy gate to define a first recess and expose a semiconductor material; depositing a gate dielectric in the first recess and along at least three sides of the semiconductor material; depositing a p-type work function tuning layer in the first recess, wherein depositing the p-type work function tuning layer comprises: depositing one or more first nitride monolayers; depositing one or more carbide monolayers on the one or more first nitride monolayers in situ with the one or more first nitride monolayers; and depositing a fill metal in the first recess over the p-type work function tuning layer.
2. The method of claim 1, wherein depositing the p-type work function tuning layer further comprises: depositing one or more second nitride monolayers on the one or more carbide monolayers.
3. The method of claim 2, wherein depositing the one or more first nitride monolayers comprises: pulsing a metal-comprising precursor in a deposition chamber where the p-type work function tuning layer is deposited; purging the metal-comprising precursor from the deposition chamber; and pulsing a nitrogen-comprising precursor in the deposition chamber.
4. The method of claim 3, wherein the metal-comprising precursor is $\text{TiCl}_{4.4}$ or $\text{TaCl}_{5.5}$, and the nitrogen-comprising precursor is NH_3 .
5. The method of claim 3, wherein depositing the one or more first nitride monolayers further comprises purging the nitrogen-comprising precursor from the deposition chamber.
6. The method of claim 1, wherein depositing the one or more carbide monolayers comprises: pulsing a metal-comprising precursor in a deposition chamber where the p-type work function tuning layer is deposited; purging the metal-comprising precursor from the deposition chamber; pulsing a carbon-comprising precursor in the deposition chamber; and purging the carbon-comprising precursor from the deposition chamber.
7. The method of claim 6, wherein the metal-comprising precursor is $\text{TiCl}_{4.4}$ or $\text{TaCl}_{5.5}$, and wherein the carbon-comprising precursor is trimethylaluminum (TMA) or aluminum triethyl (TEA).
8. The method of claim 1, wherein the method further comprises prior to depositing the fill metal, depositing an n-type work function tuning layer over the p-type work function tuning layer.
9. A device comprising: a first source/drain region and a second source/drain region; a first gate between the first source/drain region and the second source/drain region, the first gate comprising: a first gate dielectric; and a first gate electrode over the first gate dielectric, the first gate electrode comprising: a first p-type work function tuning metal over the first gate dielectric, the first p-type work function tuning metal comprising carbon and nitrogen; and a first fill metal over the first p-type work function tuning metal; a third source/drain region and a fourth source/drain region; and a second gate between the third source/drain region and the fourth source/drain region, the second gate comprising: a second gate dielectric; and a second gate electrode over the second gate dielectric, the second gate electrode comprising: a second p-type work function tuning metal over the second gate dielectric, the second p-type work function tuning metal comprising carbon and nitrogen, a first carbon to nitrogen ratio of the first p-type work function tuning metal is different

from a second carbon to nitrogen ratio of the second p-type work function tuning metal; and a second fill metal over the second p-type work function tuning metal.

10. The device of claim 9, wherein the first carbon to nitrogen ratio is in a range of 0.05 to 0.55.

11. The device of claim 9, wherein the second carbon to nitrogen ratio is in a range of 0.05 to 0.55.

12. The device of claim 9, wherein the first gate electrode further comprises an n-type work function metal over the first p-type work function tuning metal.

13. The device of claim 9, wherein the first p-type work function tuning metal further comprises titanium or tantalum.

14. A device, comprising: a semiconductor structure; a source/drain region adjacent the semiconductor structure; an interlayer dielectric over the source/drain region; a first gate over and along sidewalls of the semiconductor structure, the first gate being adjacent to the source/drain region, the first gate comprising: a gate dielectric; and a p-type work function tuning metal over the gate dielectric, the p-type work function tuning metal comprising TiCN or TaCN; and a fill metal over the p-type work function tuning metal; and a source/drain contact extending through the interlayer dielectric to electrically couple to the source/drain region, wherein the source/drain contact comprises a conductive liner and a conductive material, wherein the conductive liner spaces the conductive material from the interlayer dielectric, and wherein the conductive liner has a different composition than the conductive material.

15. The device of claim 14, wherein the p-type work function tuning metal comprises TiCN.

16. The device of claim 14, wherein the p-type work function tuning metal comprises TaCN.

17. The device of claim 14, wherein the first gate further comprises: an n-type work function tuning metal over the p-type work function tuning metal and under the fill metal.

18. The device of claim 17, wherein the first gate further comprises: an adhesive layer over the n-type work function tuning metal and under the fill metal.

19. The device of claim 14, wherein a ratio of carbon to nitrogen in the p-type work function tuning metal is in a range of 0.05 to 0.55.

20. The device of claim 14, wherein the gate dielectric comprises: an interfacial layer; and a high-k dielectric layer over the interfacial layer.
